Growth of Metamorphic InGaAs on GaAs(111)A: Counteracting Lattice Mismatch by Inserting a Thin InAs Interlayer

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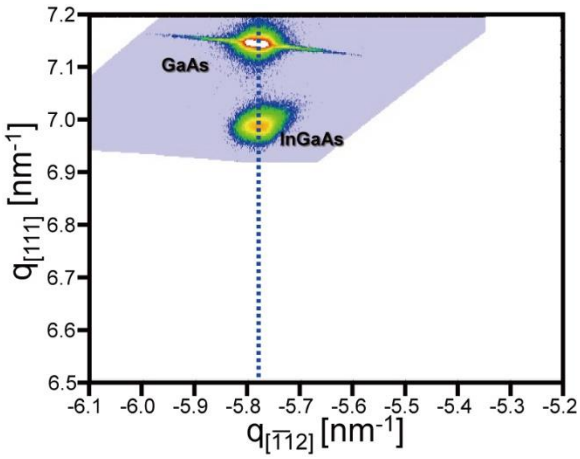

Figure S1. XRD-RSM around asymmetric 115 reflections of 80 nm-$In_{0.25}Ga_{0.75}As$ on GaAs (111)A. As indicated by the blue dotted lines, the in-plane lattice constant ($d_{\bar{1}\bar{1}2}$) of InGaAs is nearly matched to that of GaAs substrate.